Amendments to the Specification

Please amend paragraph **[0029]** on page 9 as follows:

[0029] An exemplary preferred embodiment is initially described with reference to Figs. 1-5. Referring to Fig. 1, there diagrammatically depicted is a substrate fragment 10. In one exemplary embodiment, substrate fragment 10 is a semiconductor substrate, for example comprising a substrate 12 comprising some material ~~12~~ which preferably includes some semiconductive material and may, of course, include multiple materials and layers. In the context of this document, the term "semiconductor substrate" or "semiconductive substrate" is defined to mean any construction comprising semiconductive material, including, but not limited to, bulk semiconductive materials such as a semiconductive wafer (either alone or in assemblies comprising other materials thereon), and semiconductive material layers (either alone or in assemblies comprising other materials). The term "substrate" refers to any supporting structure, including, but not limited to, the semiconductive substrates described above. ~~Substrate 10~~ Substrate 12 is positioned within a suitable deposition chamber. A first species AB has been chemisorbed to form a first species

monolayer 14 onto substrate 12 within the deposition chamber from a suitable gaseous precursor.

Please amend paragraph **[0035]** on page 12 as follows:

[0035] By way of example only, Fig. 6 diagrammatically depicts an alternate embodiment substrate fragment 10a. Like numerals from the first described embodiment are utilized where appropriate, with differences being designated with different letters or with the suffix "a". Substrate fragment 10a is shown at a processing step subsequent to that depicted by Fig. 3 with respect to substrate fragment 10. A first species DB has been chemisorbed to form a first species monolayer 14a onto the substrate, here onto species AO, within the deposition chamber from a suitable gaseous precursor. For example, and by way of example only, oxide AO might comprise one or the other of tin oxide and indium oxide, with first species DB comprising the other of a tin or indium containing species, and with "D" designating one of the tin or indium, and the "A" designating the other of tin or indium.